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B

11(Amended). A process as claimed in claim 1, comprising mask steps 1, 2, 3, 4, 5, 6, 8, 10, 11, 12, 13, 14, 15, and 16.

20(Added). A method as claimed in claim 1, wherein:

a) step 1 comprises the sub-steps of:

- (i) using P- bulk Silicon as a starting material;
- (ii) performing an initial oxidation;
- (iii) performing a photolithographic step;
- (iv) performing an N-Type Implant to create said N-Well; and
- (v) performing a diffusion;

b) step 2 comprises the sub-steps of:

- (i) performing an oxide etch;
- (ii) performing an oxidation;
- (iii) performing a silicon nitride deposition;
- (iv) performing a photolithographic step; and
- (v) performing a nitride etch;

c) step 3 comprises the sub-steps of:

- (i) performing a photolithographic step;
- (ii) performing a P-Type Implant;
- (iii) performing a blanket N-Type Implant;
- (iv) performing an oxidation step to form a field oxide;
- (v) performing a nitride etch;
- (vi) performing an oxide etch; and
- (vii) performing an oxidation to form a pre-gate oxide;

d) step 4 comprises the sub-steps of:

- (i) performing an oxide etch
- (ii) performing an oxidation the gate oxide; and
- (iii) performing a photolithographic step;

e) step 5 comprises the sub-steps of:

- (i) performing an oxide etch;
- (ii) performing an oxidation to form said thin gate oxide;

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(iii) performing a photolithographic step;

(iv) performing a P-Type Implant;

f) step 6 comprises the sub-steps of:

(i) performing polysilicon gate deposition;

(ii) performing polysilicon doping;

(iii) performing a photolithographic step;

(iv) performing a polysilicon etch;

g) step 7 comprises the sub-steps of:

(i) performing a photolithographic step;

(ii) performing a P-type implant to form the P-base;

h) step 8 comprises the sub-steps of:

(i) performing a photolithographic step;

(ii) performing an N-type implant;

i) step 9 comprises the sub-steps of:

(i) performing a photolithographic step;

(ii) performing a P-type implant;

j) step 10 comprises the sub-steps of:

(i) performing an oxidation and diffusion step;

(ii) performing a polysilicon oxidation;

(iii) performing a photolithographic step; and

(iv) performing an N-type implant to create said N⁺ implant region;

k) step 11 comprises the sub-steps of:

(i) performing a photolithographic step; and

(ii) performing a P-type implant to create said P⁺ implant region;

l) step 12 comprises the sub-steps of:

(i) performing a SG/PSG/SOG deposition;

(ii) performing a diffusion step; and

(iii) performing a photolithographic step; and

(iv) performing a contact etch;

m) step 13 comprises the sub-steps of:

(i) performing a Ti/TiN deposition with oxidation;

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- (ii) performing an aluminum alloy deposition;
- (iii) performing a photolithographic step;
- (iv) performing a metal etch; and
- (v) performing dielectric and SOG deposition;

(n) step 14 comprises the sub-steps of:

- (i) performing a photolithographic step; and
- (ii) etching said vias; and

(o) step 15 comprises the sub-steps of:

- (i) performing Ti/TiN deposition with oxidation;
- (ii) performing an aluminum alloy deposition;
- (iii) performing a photolithographic step;
- (iv) performing a metal etch;
- (v) performing an oxide/nitride deposition;
- (vi) performing a photolithographic step; and
- (vii) performing an oxide etch.